Nand Flash Memory Technologies Ieee Press Series

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2019 IEEE International Conference on Intelligent Systems and Green Technology (ICISGT) MDPI
A Flash memory is a Non Volatile Memory (NVM) whose "unit cells" are fabricated in CMOS technology and programmed and erased electrically. In 1971, Frohman-Bentchkowsky developed a folating polysilicon gate tran sistor [1, 2], in which hot electrons were injected in the floating gate and removed by either Ultra-Violet (UV) internal photoemission or by Fowler Nordheim tunneling. This is the "unit cell" of EPROM (Electrically Pro grammable Read Only Memory), which, consisting of a single transistor, can be very densely integrated. EPROM memories are electrically programmed and erased by UV exposure for 20-30 mins. In the late 1970s, there have been many efforts to develop an electrically erasable EPROM, which resulted in EEPROMs (Electrically Erasable Programmable ROMs). EEPROMs use hot electron tunneling for program and Fowler-Nordheim tunneling for erase. The EEPROM cell consists of two transistors and a tunnel oxide, thus it is two or three times the size of an EPROM. Successively, the combination of hot carrier programming and tunnel erase was rediscovered to achieve a single transistor EEPROM, called Flash EEPROM. The first cell based on this concept has been presented in 1979 [3]; the first commercial product, a 256K memory chip, has been presented by Toshiba in 1984 [4]. The market did not take off until this technology was proven to be reliable and manufacturable [5].
Emerging Memory and Computing Devices in the Era of Intelligent Machines Springer Science & Business Media
Digital photography, MP3, digital video, etc. make extensive use of NAND-based Flash cards as storage media. To realize how much NAND Flash memories pervade every aspect of our life, just imagine how our recent habits would change if the NAND memories suddenly disappeared. To take a picture it would be necessary to find a film (as well as a traditional camera...), disks or even magnetic tapes would be used to record a video or to listen a song, and a cellular phone would return to be a simple mean of communication rather than a multimedia console. The development of NAND Flash memories will not be set down on the mere evolution of personal entertainment systems since a new killer application can trigger a further success: the replacement of Hard Disk Drives (HDDs) with Solid State Drives (SSDs). SSD is made up by a microcontroller and several NANDs. As NAND is the technology driver for IC circuits, Flash designers and technologists have to deal with a lot of challenges. Therefore, SSD (system) developers must understand Flash technology in order to exploit its benefits and countermeasure its weaknesses. Inside NAND Flash Memories is a comprehensive guide of the NAND world: from circuits design (analog and digital) to Flash reliability (including radiation effects), from testing issues to high-performance (DDR) interface, from error correction codes to NAND applications like Flash cards and SSDs.
Flash Memories Springer Science & Business Media
This book provides a comprehensive reference for both academia and industry on the fundamentals, technology details, and applications of Advanced Driver-Assistance Systems (ADAS) and autonomous driving, an emerging and rapidly growing area. The book written by experts covers the most recent research results and industry progress in the following areas: ADAS system design and test methodologies, advanced materials, modern automotive technologies, artificial intelligence, reliability concerns, and failure analysis in ADAS. Numerous images, tables, and didactic schematics are included throughout. This essential book equips readers with an in-depth understanding of all aspects of ADAS, providing insights into key areas for future research and

development. • Provides comprehensive coverage of the state-of-the-art in ADAS • Covers advanced materials, deep learning, quality and reliability concerns, and fault isolation and failure analysis • Discusses ADAS system design and test methodologies, novel automotive technologies • Features contributions from both academic and industry authors, for a complete view of this important technology

Nonvolatile Memory Technologies with Emphasis on Flash Springer Science & Business Media

Offers a comprehensive overview of NAND flash memories, with insights into NAND history, technology, challenges, evolutions, and perspectives Describes new program disturb issues, data retention, power consumption, and possible solutions for the challenges of 3D NAND flash memory Written by an authority in NAND flash memory technology, with over 25 years' experience

Inside Solid State Drives (SSDs) Springer Science & Business Media

This book discusses the new roles that the VLSI (very-large-scale integration of semiconductor circuits) is taking for the safe, secure, and dependable design and operation of electronic systems. The book consists of three parts. Part I, as a general introduction to this vital topic, describes how electronic systems are designed and tested with particular emphasis on dependability engineering, where the simultaneous assessment of the detrimental outcome of failures and cost of their containment is made. This section also describes the related research project "Dependable VLSI Systems," in which the editor and authors of the book were involved for 8 years. Part II addresses various threats to the dependability of VLSIs as key systems components, including time-dependent degradations, variations in device characteristics, ionizing radiation, electromagnetic interference, design errors, and tampering, with discussion of technologies to counter those threats. Part III elaborates on the design and test technologies for dependability in such applications as control of robots and vehicles, data processing, and storage in a cloud environment and heterogeneous wireless telecommunications. This book is intended to be used as a reference for engineers who work on the design and testing of VLSI systems with particular attention to dependability. It can be used as a textbook in graduate courses as well. Readers interested in dependable systems from social and industrial–economic perspectives will also benefit from the discussions in this book.

3D Flash Memories Springer Science & Business

This conference brings the memory community together in a workshop environment to discuss the memory process and design technologies, applications, market needs and strategies It is sponsored by the IEEE Electron Devices Society and meets annually in May Although it is the seventh IMW meeting to be held this year, it has a long history of Non Volatile Semiconductor Memory Workshops (NVSMW) dating back to 1976 In 2008, NVSMW and the International Conference on Memory Technology and Design (ICMTD) merged to incorporate both the volatile and non volatile memory aspects in one forum while maintaining the workshop experience And the scope was extended from non volatile memory technology and design, which had been successfully discussed in more than 30 years of NVSMW, to the other memory technologies, which were the focus of ICMTD

2019 IEEE 11th International Memory Workshop (IMW) Woodhead Publishing

The revised second edition of this respected text provides a state-of-the-art overview of the main topics relating to solid state drives (SSDs), covering NAND flash memories, memory controllers (including booth hardware and software), I/O interfaces (PCIe/SAS/SATA), reliability, error correction codes (BCH and LDPC), encryption, flash signal processing and hybrid storage. Updated throughout to include all recent work in the field, significant changes for the new edition include: A new chapter on flash memory errors and data recovery procedures in SSDs for reliability and lifetime improvement Updated coverage of SSD Architecture and PCI Express Interfaces moving from PCIe Gen3 to PCIe Gen4 and including a section on NVMe over fabric (NVMf) An additional section on 3D flash memories An update on standard reliability procedures for SSDs Expanded coverage of BCH for SSDs, with a specific section on detection A new section on non-binary Low-Density Parity-Check (LDPC) codes, the most recent advancement in the field A description of randomization in the protection of SSD data against attacks, particularly relevant to 3D architectures The SSD market is booming, with many industries placing a huge effort in this space, spending billions of dollars in R&D and product development. Moreover, flash manufacturers are now moving to 3D architectures, thus enabling an even higher level of storage capacity. This book takes the reader through the fundamentals and brings them up to speed with the most recent developments in the field, and is suitable for advanced students, researchers and engineers alike.

CMOS Processors and Memories NAND Flash Memory Technologies

This book describes the basic technologies and operation principles of charge-trapping non-volatile memories. The authors explain the device physics of each device architecture and provide a concrete description of the materials involved as well as the fundamental properties of the technology. Modern material properties used as charge-trapping layers, for new applications are introduced.

Advanced Driver Assistance Systems and Autonomous Vehicles John Wiley & Sons

This book provides a comprehensive introduction to embedded flash memory, describing the history, current status, and future projections for technology, circuits, and systems applications. The authors describe current main-stream embedded flash technologies from floating-gate 1Tr, floating-gate with split-gate (1.5Tr), and 1Tr/1.5Tr SONOS flash technologies and their successful creation of various applications. Comparisons of these embedded flash technologies and future projections are also provided. The authors demonstrate a variety of embedded applications for auto-motive, smart-IC cards, and low-power, representing the leading-edge technology developments for eFlash. The discussion also includes insights into future prospects of application-driven non-volatile memory technology in the era of smart advanced automotive system, such as ADAS (Advanced Driver Assistance System) and IoE (Internet of Everything). Trials on technology convergence and future prospects of embedded non-volatile memory in the new memory hierarchy are also described. Introduces the history of embedded flash memory technology for micro-controller products and how embedded flash innovations developed; Includes comprehensive and detailed descriptions of current main-stream embedded flash memory technologies, sub-system designs and applications; Explains why embedded flash memory requirements are different from those of stand-alone flash memory and how to achieve specific goals with technology development and circuit designs; Describes a mature and stable floating-gate 1Tr cell technology imported from stand-alone flash memory products - that then introduces embedded-specific split-gate memory cell technologies based on floating-gate storage structure and charge-trapping SONOS technology and their eFlash sub-system designs; Describes automotive and smart-IC card applications requirements and achievements in advanced eFlash beyond 4 0nm node.

2021 32nd Irish Signals and Systems Conference (ISSC) Springer

Meeting of academia and research professionals to discuss reliability challenges

VLSI Memory Chip Design John Wiley & Sons

Flash memories and memory systems are key resources for the development of electronic products implementing converging technologies or exploiting solid-state memory disks. This book illustrates state-of-the-art technologies and research studies on Flash memories. Topics in modeling, design, programming, and materials for memories are covered along with real application examples.

Selected Advances in Nanoelectronic Devices Springer Nature

Presented here is an all-inclusive treatment of Flash technology, including Flash memory chips, Flash embedded in logic, binary cell Flash, and multilevel cell Flash. The book begins with a tutorial of elementary concepts to orient readers who are less familiar with the subject. Next, it covers all aspects and variations of Flash technology at a mature engineering level: basic device structures, principles of operation, related process technologies, circuit design, overall design tradeoffs, device testing, reliability, and applications.

Wiley-IEEE Press

Advances of Computer Science & Engineering, Electrical and Electronics areas in view of use to humanity Interdisciplinary research that may lead to benefit the humanity Research contributions can also be presented in Spanish, Russian, Portuguese, Persian, French languages This is first of its kind in India and only the English version will be exported to IEEExplore

In Search of the Next Memory Springer Nature

Silicon Devices and Process Integration covers state-of-the-art silicon devices, their characteristics, and their interactions with process parameters. It serves as a comprehensive guide which addresses both the theoretical and practical aspects of modern silicon devices and the relationship between their electrical properties and processing conditions. The book is compiled from the author's industrial and academic lecture notes and reflects years of experience in the development of silicon devices. Features include: A review of silicon properties which provides a foundation for understanding the device properties discussion, including mobility-enhancement by straining silicon; State-of-the-art technologies on high-K gate dielectrics, low-K dielectrics, Cu interconnects, and SiGe BiCMOS; CMOS-only applications, such as subthreshold current and parasitic latch-up; Advanced Enabling processes and process integration. This book is written for engineers and scientists in semiconductor research, development and manufacturing. The problems at the end of each chapter and the numerous charts, figures and tables also make it appropriate for use as a text in graduate and advanced undergraduate courses in electrical engineering and materials science.

Emerging Memory Technologies Springer Science & Business Media

CMOS Processors and Memories addresses the-state-of-the-art in integrated circuit design in the context of emerging computing systems. New design opportunities in memories and processor are discussed. Emerging materials that can take system performance beyond standard CMOS, like carbon nanotubes, graphene, ferroelectrics and tunnel junctions are explored. CMOS Processors and Memories is divided into two parts: processors and memories. In the first part we start with high performance, low power processor design, followed by a chapter on multi-core processing. They both represent state-of-the-art concepts in current computing industry. The third chapter deals with asynchronous design that still carries lots of promise for future computing needs. At the end we present a "hardware design space exploration" methodology for implementing and analyzing the hardware for the Bayesian inference framework. This particular methodology involves: analyzing the computational cost and exploring candidate hardware components, proposing various custom architectures using both traditional CMOS and hybrid nanotechnology CMOL. The first part concludes with hybrid CMOS-Nano architectures. The second, memory part covers state-of-the-art SRAM, DRAM, and flash memories as well as emerging device concepts. Semiconductor memory is a good example of the full custom design that applies various analog and logic circuits to utilize the memory cell's device physics. Critical physical effects that include tunneling, hot electron injection, charge trapping (Flash memory) are discussed in detail. Emerging memories like FRAM, PRAM and ReRAM that depend on magnetization, electron spin alignment, ferroelectric effect, built-in potential well, quantum effects, and thermal melting are also described. CMOS Processors and Memories is a must for anyone serious about circuit design for future computing technologies. The book is written by top notch international experts in industry and academia. It can be used in graduate course curriculum.

Vertical 3D Memory Technologies Springer

This book covers semiconductor memory technologies from device bit-cell structures to memory array design with an emphasis on recent industry scaling trends and cutting-edge technologies. The first part of the book discusses the mainstream semiconductor memory technologies. The second part of the book discusses the emerging memory candidates that may have the potential to change the memory hierarchy, and surveys new applications of memory technologies for machine/deep learning applications. This book is intended for graduate students in electrical and computer engineering programs and researchers or industry professionals in semiconductors and microelectronics. Explains the design of basic memory bit-cells including 6-transistor SRAM, 1-transistor-1-capacitor DRAM, and floating gate/charge trap FLASH transistor Examines the design of the peripheral circuits including the sense amplifier and array-level organization for the memory array Examines industry trends of memory technologies such as FinFET based SRAM, High-Bandwidth-Memory (HBM), 3D NAND Flash, and 3D X-point array Discusses the prospects and challenges of emerging memory technologies such as PCM, RRAM, STT-MRAM/SOT-MRAM and FeRAM/FeFET Explores the new applications such as in-memory computing for AI hardware acceleration.

VLSI Design and Test for Systems Dependability Springer Nature

Semiconductor Memories and Systems provides a comprehensive overview of the current state of semiconductor memory at the technology and system levels. After an introduction on market trends and memory applications, the book focuses on mainstream technologies, illustrating their current status, challenges and opportunities, with special attention paid to scalability paths. Technologies discussed include static random access memory (SRAM), dynamic random access memory (DRAM), non-volatile memory (NVM), and NAND flash memory. Embedded memory and requirements and system level needs for storage class memory are also addressed. Each chapter covers physical operating mechanisms, fabrication technologies, and the main challenges to scalability. Finally, the work reviews the emerging trends for storage class memory, mainly focusing on the advantages and opportunities of phase change based memory technologies. Features contributions from experts from leading companies in semiconductor memory Discusses physical operating mechanisms, fabrication technologies and paths to scalability for current and emerging semiconductor memories Reviews primary memory technologies, including SRAM, DRAM, NVM and NAND flash memory Includes emerging storage class memory technologies such

as phase change memory
Silicon Devices and Process Integration John Wiley & Sons
This comprehensive reference book provides electronics engineers with the technical data and perspective necessary for the intelligent selection, specification, and application of nonvolatile semiconductor memory devices. A "one-stop shopping" tool for the working engineer, this book presents the fundamental aspects of nonvolatile semiconductor memory technologies, devices, reliability, and applications.
Machine Learning and Non-volatile Memories Springer
This book walks the reader through the next step in the evolution of NAND flash memory technology, namely the development of 3D flash memories, in which multiple layers of memory cells are grown within the same piece of silicon. It describes their working principles, device architectures, fabrication techniques and practical implementations, and highlights why 3D flash is a brand new technology. After reviewing market trends for both NAND and solid state drives (SSDs), the book digs into the details of the flash memory cell itself, covering both floating gate and emerging charge trap technologies. There is a plethora of different materials and vertical integration schemes out there. New memory cells, new materials, new architectures (3D Stacked, BiCS and P-BiCS, 3D FG, 3D VG, 3D advanced architectures); basically, each NAND manufacturer has its own solution. Chapter 3 to chapter 7 offer a broad overview of how 3D can materialize. The 3D wave is impacting emerging memories as well and chapter 8 covers 3D RRAM (resistive RAM) crosspoint arrays. Visualizing 3D structures can be a challenge for the human brain: this is way all these chapters contain a lot of bird's-eye views and cross sections along the 3 axes. The second part of the book is devoted to other important aspects, such as advanced packaging technology (i.e. TSV in chapter 9) and error correction codes, which have been leveraged to improve flash reliability for decades. Chapter 10 describes the evolution from legacy BCH to the most recent LDPC codes, while chapter 11 deals with some of the most recent advancements in the ECC field. Last but not least, chapter 12 looks at 3D flash memories from a system perspective. Is 14nm the last step for planar cells? Can 100 layers be integrated within the same piece of silicon? Is 4 bit/cell possible with 3D? Will 3D be reliable enough for enterprise and datacenter applications? These are some of the questions that this book helps answering by providing insights into 3D flash memory design, process technology and applications.
Charge-Trapping Non-Volatile Memories Springer Science & Business Media
This book presents the basics of both NAND flash storage and machine learning, detailing the storage problems the latter can help to solve. At a first sight, machine learning and non-volatile memories seem very far away from each other. Machine learning implies mathematics, algorithms and a lot of computation; non-volatile memories are solid-state devices used to store information, having the amazing capability of retaining the information even without power supply. This book will help the reader understand how these two worlds can work together, bringing a lot of value to each other. In particular, the book covers two main fields of application: analog neural networks (NNs) and solid-state drives (SSDs). After reviewing the basics of machine learning in Chapter 1, Chapter 2 shows how neural networks can mimic the human brain; to accomplish this result, neural networks have to perform a specific computation called vector-by-matrix (VbM) multiplication, which is particularly power hungry. In the digital domain, VbM is implemented by means of logic gates which dictate both the area occupation and the power consumption; the combination of the two poses serious challenges to the hardware scalability, thus limiting the size of the neural network itself, especially in terms of the number of processable inputs and outputs. Non-volatile memories (phase change memories in Chapter 3, resistive memories in Chapter 4, and 3D flash memories in Chapter 5 and Chapter 6) enable the analog implementation of the VbM (also called "neuromorphic architecture"), which can easily beat the equivalent digital implementation in terms of both speed and energy consumption. SSDs and flash memories are strictly coupled together; as 3D flash scales, there is a significant amount of work that has to be done in order to optimize the overall performances of SSDs. Machine learning has emerged as a viable solution in many stages of this process. After introducing the main flash reliability issues, Chapter 7 shows both supervised and un-supervised machine learning techniques that can be applied to NAND. In addition, Chapter 7 deals with algorithms and techniques for a pro-active reliability management of SSDs. Last but not least, the last section of Chapter 7 discusses the next challenge for machine learning in the context of the so-called computational storage. No doubt that machine learning and non-volatile memories can help each other, but we are just at the beginning of the journey; this book helps researchers understand the basics of each field by providing real application examples, hopefully, providing a good starting point for the next level of development.